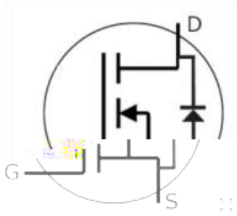
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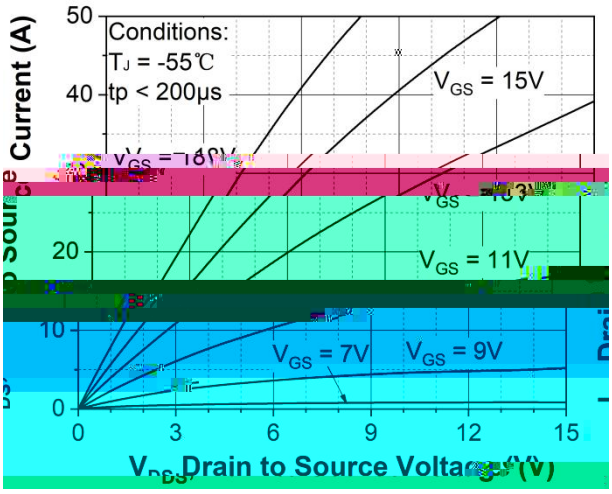
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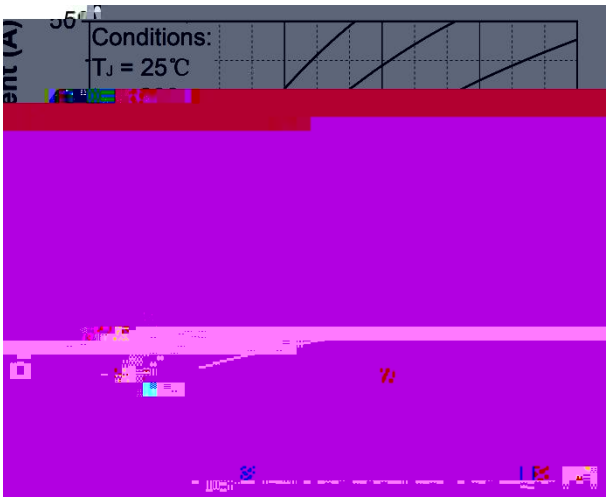
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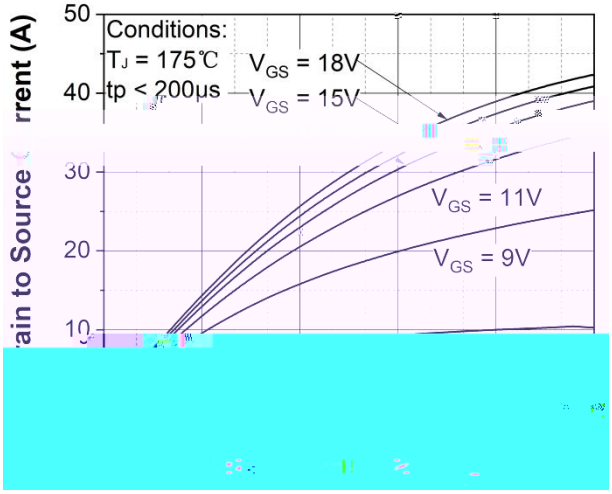
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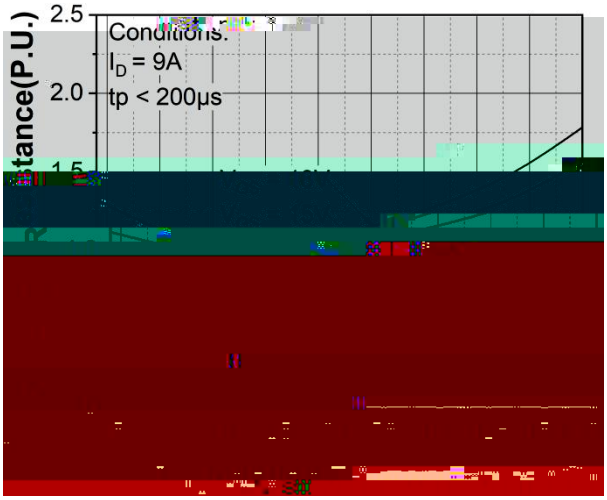
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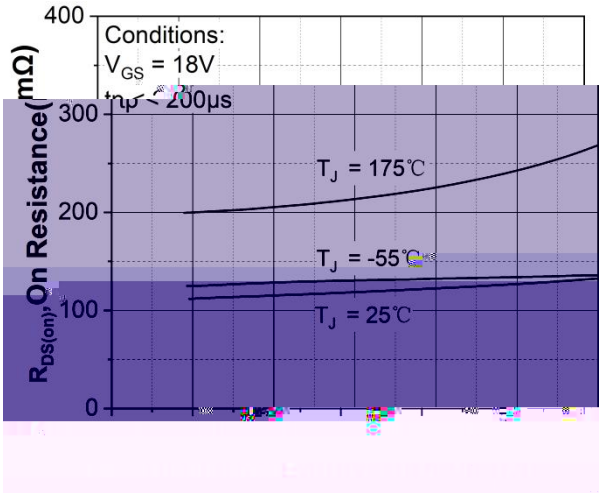
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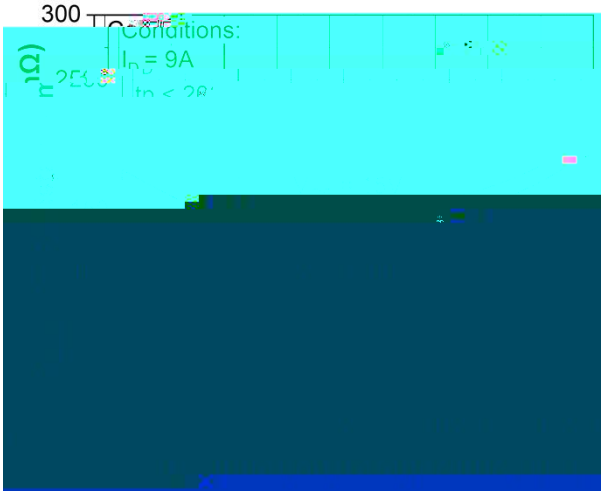

Conditions:
T_J = -55℃
tp < 200μs
V_{GS} = 15V
V_{GS} = 11V
V_{GS} = 7V
V_{GS} = 9V
50
40
20
10
0
0
3
6
9
12
15
Current (A)
Drain to Source Voltage (V)

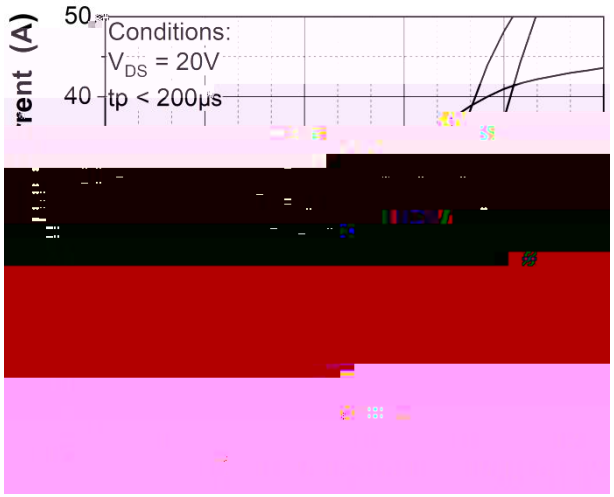

Conditions:
T_J = 25℃

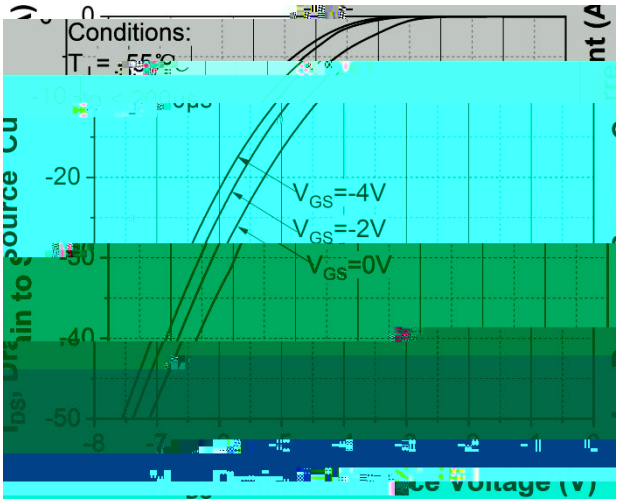

Conditions:
T_J = 175℃
tp < 200μs
V_{GS} = 18V
V_{GS} = 15V
V_{GS} = 11V
V_{GS} = 9V
50
40
30
20
10

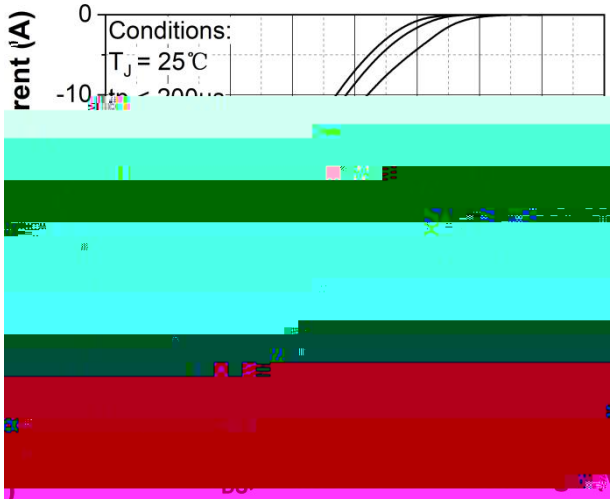

Conditions:
I_D = 9A
tp < 200μs
2.5
2.0

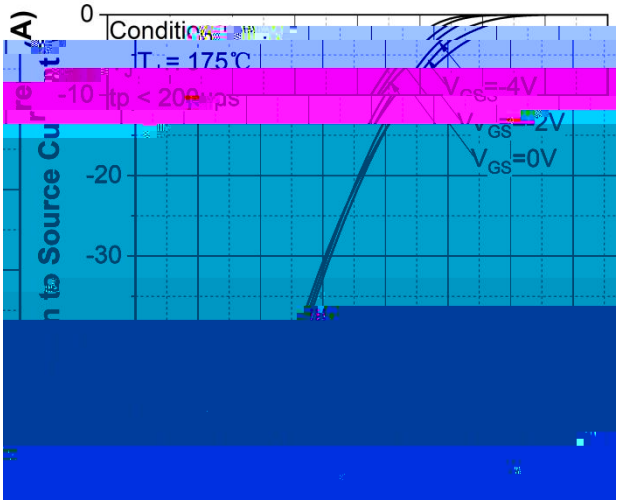

Conditions:
V_{GS} = 18V
tp < 200μs
T_J = 175℃
T_J = -55℃
T_J = 25℃
400
300
200
100
0
On Resistance(mΩ)

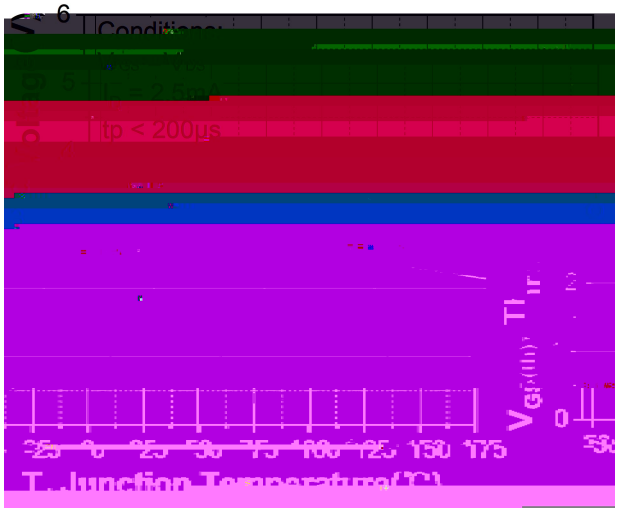

Conditions:
I_D = 9A
300

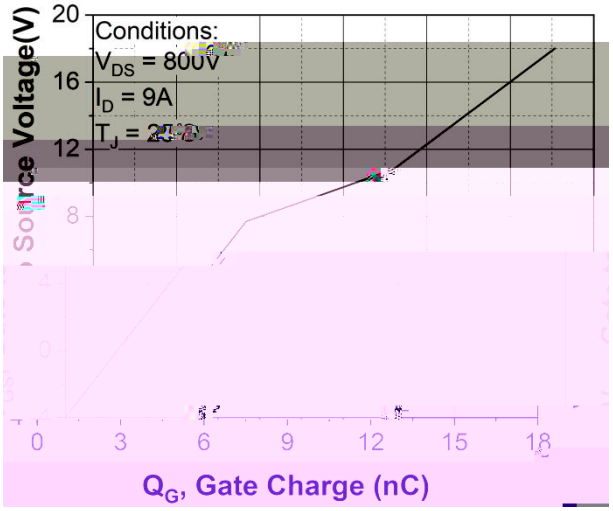

50
40
Conditions:
V_{DS} = 20V
tp < 200μs

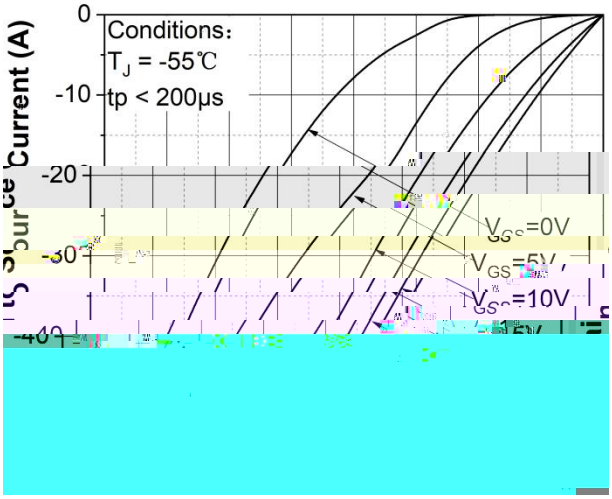

0
-20
-40
-50
-8
V_{GS}=-4V
V_{GS}=-2V
V_{GS}=0V

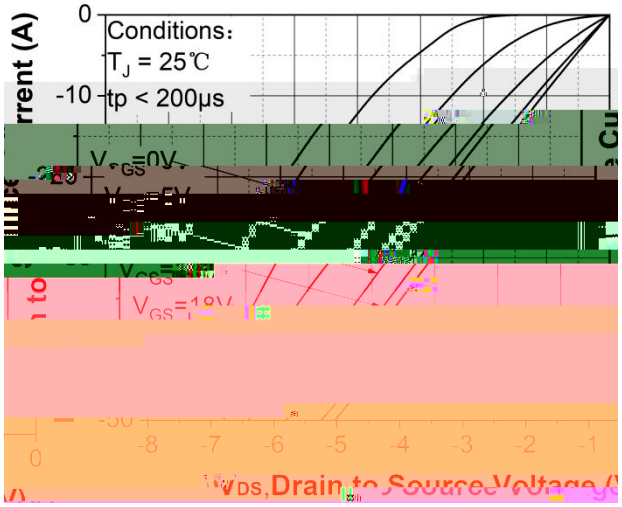

0
-10
Conditions:
T_J = 25℃

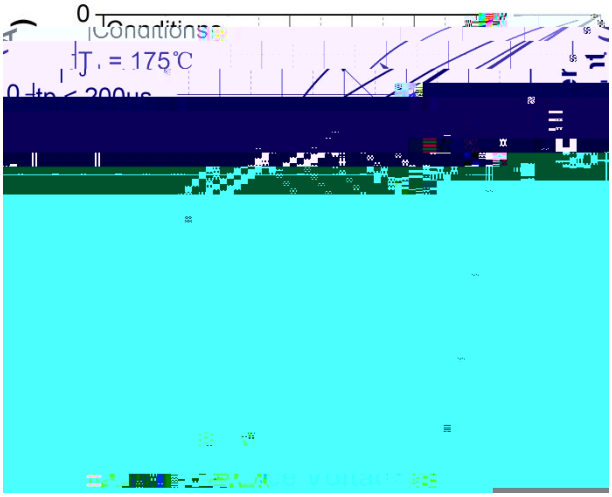

0
-10
-20
-30
V_{GS}=-4V
V_{GS}=0V

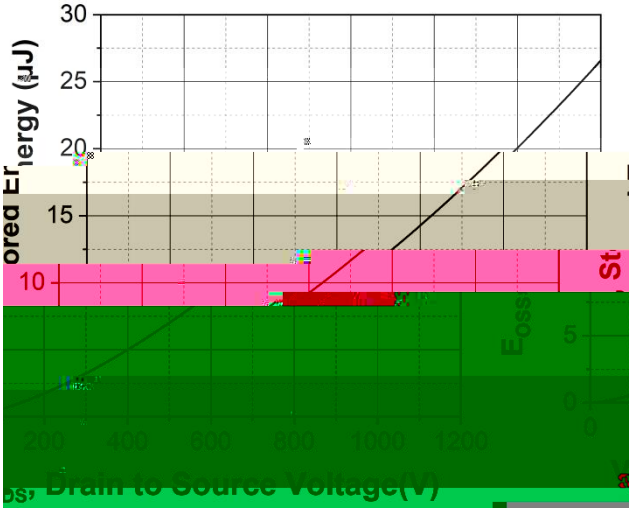

6
tp < 200μs
0

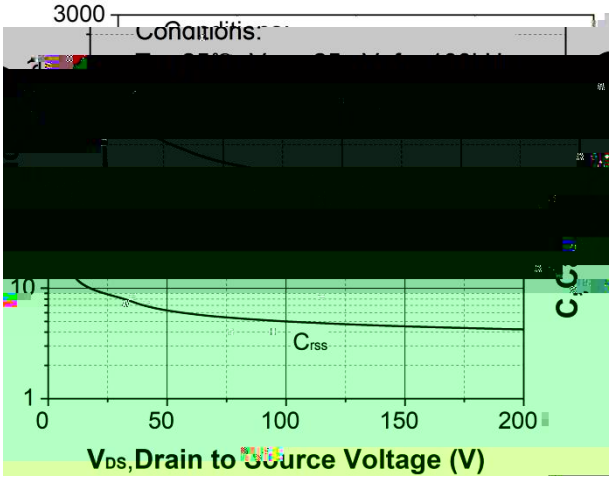

20
16
12
8
Conditions:
V_{DS} = 800V
I_D = 9A
0
3
6
9
12
15
18
Q_G, Gate Charge (nC)

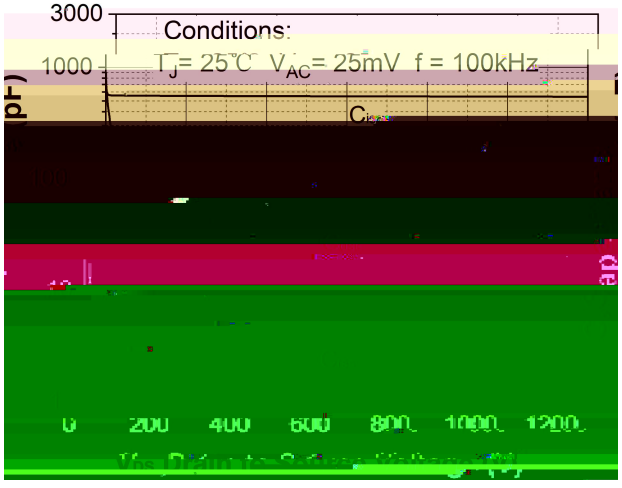

Conditions:
T_J = -55℃
tp < 200μs
V_{GS}=0V
V_{GS}=5V
V_{GS}=10V

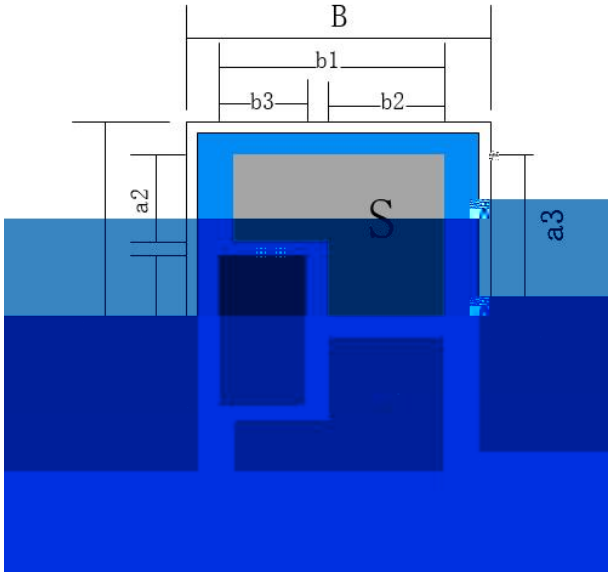

Conditions:
T_J = 25℃
tp < 200μs
V_{GS}=0V
V_{GS}=5V
V_{GS}=10V
V_{DS},Drain to Source Voltage


Conditions:
T_J = 175℃
tp < 200μs


Energy (μJ)
E_{OSS}
V_{DS}, Drain to Source Voltage(V)


Conditions:
C_{rss}
V_{DS},Drain to Source Voltage (V)


Conditions:
T_J= 25℃ V_{AC}= 25mV f = 100kHz
C_{oss}


B
b1
b3
b2
a2
S
a3

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